

10/780,572

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	10/780572	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/11 16:14
L2	2	09/934550	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/11 16:18
L3	1	("6057081").PN.	USPAT	OR	OFF	2005/10/11 16:18
L4	1	("6351406").PN.	USPAT	OR	OFF	2005/10/11 16:18
L5	1	("6104324").PN.	USPAT	OR	OFF	2005/10/11 16:19
L6	1	("5060191").PN.	USPAT	OR	OFF	2005/10/11 16:19
L7	2	2002/0017667	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/11 16:21
L8	1	("6351406").PN.	USPAT	OR	OFF	2005/10/11 16:24
L9	0	(ferroelectronic adj memory) and (first adj signal adj electrodes) and (second adj signal adj electrodes) and ferroelectric and memory and cell and matrix and array and (peripheric adj circuit) and direction	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/11 16:29
L10	0	(ferroelectronic adj memory) and (first adj signal adj electrodes) and (second adj signal adj electrodes) and ferroelectric and memory and cell and matrix and array and (peripheric adj circuit)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/11 16:28
L11	0	(ferroelectronic adj memory) and (signal adj electrodes) and ferroelectric and memory and cell and matrix and array and (peripheric adj circuit) and direction	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/11 16:28
L12	1	(ferroelectronic adj memory) and (first adj signal adj electrodes) and (second adj signal adj electrodes) and ferroelectric and memory and cell and matrix and array and direction	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/11 16:34

L13	1	("6727536").PN.	USPAT	OR	OFF	2005/10/11 16:32
L14	1	8 and (ferroelectric or memory or device or first or signal or electrodes or second or cell or matrix or array or direction or intersection or intersecting or writing or reading or information or microcrystalline or amorphous or heat or treatment or peripheral or circuit or dielectric)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/11 16:54
L15	1	3 and (ferroelectric or memory or device or first or signal or electrodes or second or cell or matrix or array or direction or intersection or intersecting or writing or reading or information or microcrystalline or amorphous or heat or treatment or peripheral or circuit or dielectric)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/11 16:57
L16	1	6 and (ferroelectric or memory or device or first or signal or electrodes or second or cell or matrix or array or direction or intersection or intersecting or writing or reading or information or microcrystalline or amorphous or heat or treatment or peripheral or circuit or dielectric)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/11 17:14
L17	2661	438/3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/11 17:14
L18	3418	438/257	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/11 17:15
L19	1592	438/166	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/11 17:15
L20	2466	438/197	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/11 17:15

L21	1429	438/381	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/11 17:15
L22	1423	438/680	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/11 17:15
L23	666	438/681	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/11 17:15
L24	4122	438/692	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/11 17:15
L25	2341	438/706	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/11 17:15
L26	990	438/712	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/11 17:15